Chapter 1

Raman spectroscopy for practical characterization of single-walled carbon nanotubes in various environments

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Features of Raman scattering spectroscopy as a practical characterization tool of single-walled carbon nanotubes (SWCNTs) samples are reviewed. After the basic introduction of G-band, D-band, radial breathing mode (RBM), and 2D-band (G’-band) peaks, chirality dependent G⁺, G⁻ features, doping effect, and resonance energy profiles are reviewed. Kataura plot; optical transition energy vs. RBM Raman shift; is the essential tool for the practical analysis of SWCNT sample. Available experimental data and correlation are summarized as the Kataura plot. The Raman shift and transition energy shift depending on SWCNT morphologies such as directly-grown sample on substrates, vertically-aligned sample, horizontally-aligned sample, suspended sample, and micelle-wrapped chirality-selected samples are compared. The detailed discussion of the environmental effect on Kataura plot follows. Finally, the temperature dependence of Raman features is discussed.

Contents

1. Raman scattering spectra from SWCNTs ........................................... 2
  1.1. G-band ................................................................. 2
  1.2. D-band ................................................................. 6
  1.3. RBM peaks ............................................................ 7
  1.4. Kataura plots ......................................................... 9
2. Environmental effects on Kataura plots ........................................... 10
  2.1. Raman shift ......................................................... 10
  2.2. Resonance energy .................................................. 13
  2.3. Temperature dependence ........................................... 15
3. Acknowledgments ................................................................. 17
References ................................................................. 17

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Reminiscences of Millie

Raman spectroscopy of carbon nanotubes cannot be discussed without Millie. She has been the leader or the mentor of the initiation, development in experiment and in theory, and documentation of this research field. We have joined this exciting research field by the direct guidance of Millie. We witness that Millie was surprisingly kind and fair to new comers to the field. We can find so many researchers around the world who feel Millie as their direct mentor. Her initiatives, passion, and devote to science are always encouraging us and guiding us to continue research. We thank Millie for these immortal gifts.

1. Raman scattering spectra from SWCNTs

After the discovery of single-walled carbon nanotubes (SWCNTs),\textsuperscript{1,2} Raman scattering spectroscopy is one of the most important analytical tools.\textsuperscript{3} In Raman scattering spectra from SWCNT samples, the characteristic peaks appear and they come mainly from the phonon scattering. They are called the G-band, D-band, radial breathing mode (RBM) peaks, 2D-band (G’), and so on. The relevant phonons, Raman shift and scattering intensity of these peaks have been intensively studied. Hence, Raman scattering spectroscopy provides us plentiful information of SWCNTs. The knowledge is useful in analysis of not only SWCNTs but also the other carbon materials, especially nano-carbon materials, such as double-walled carbon nanotube, multi-walled carbon nanotube and graphene, and greatly contributes to the development of nanotechnology. The growth techniques of SWCNT samples have been proposed, such as arc-discharge methods,\textsuperscript{1,2} laser-ablation method\textsuperscript{4} and chemical vapor deposition methods,\textsuperscript{5,6} and the growth techniques have developed rapidly. SWCNTs with various morphologies can be realized; directly-growth on substrates,\textsuperscript{6} vertically-aligned growth,\textsuperscript{7,8} horizontally-aligned growth\textsuperscript{9} and suspended growth.\textsuperscript{10} At the same time, separation techniques after the growth are also developed, and we can obtain even single chirality SWCNT samples.\textsuperscript{11,12} As a result, the chirality dependence of their intrinsic physical properties are unveiled and it is found that they are affected by the morphology or the surrounding environments. The importance of Raman scattering spectroscopy is increasing for the detailed analysis of SWCNT samples. For example, Raman scattering spectra from SWCNTs, which were synthesized by using alcohol catalytic CVD (ACCVD) method,\textsuperscript{13} are shown in Fig. 1. The G-band, which includes G\textsuperscript{+} peak, G\textsuperscript{−} peak and BWF peak, D-band and RBM peaks are clearly observed. The split G-band is a characteristic feature of SWCNTs and RBM peaks are also unique to SWCNTs.

1.1. G-band

The G-band originates from an in-plane stretching mode of carbon-carbon bond in graphitic materials.\textsuperscript{14} In graphite, since the G-band comes from phonons with
$E_{2g}$ symmetry, which are equivalent longitudinal and transverse optical phonons at Γ point, the G-band appears as only one peak around 1580 cm$^{-1}$. In the contrast to the single peak in the case of graphite or graphene, the G-band from SWCNTs appear around 1590 cm$^{-1}$ as multiple peaks.\textsuperscript{15} The G-band of SWCNTs composed of multiple peaks was explained to be the superposition of peaks from phonon with different symmetry, such as $2A$, $2E_1$ and $2E_2$ modes.\textsuperscript{15} Even more complex G-band is often observed from bundled (aggregated) SWCNT samples.

Especially, two most prominent peaks among the G-band are called $G^+$ and $G^-$ peaks, and $G^-$ peak appears on the lower wavenumber side of $G^+$ peak. Raman scattering spectra are measured from not only bundled SWCNTs but also dispersed SWCNTs in solution\textsuperscript{16} and suspended SWCNTs in air.\textsuperscript{17} The G-band of single-chirality SWCNT is measured from chirality-separated SWCNT solutions or a single suspended SWCNT, and it generally exhibits only $G^+$ and $G^-$ peaks.\textsuperscript{18} Because the theory states that the intensity of $A$ mode peaks are strong,\textsuperscript{19} the $G^+$ and $G^-$ are usually assigned to $A$ symmetry phonons. The feature of $G^+$ and $G^-$ peaks from dispersed SWCNTs in solution are investigated in detail and it is found that the intensity ratio between $G^+$ and $G^-$ peaks depend on both $d_{tube}$ and the chiral angle.\textsuperscript{20}

In the case of semi-conducting SWCNTs, $G^+$ and $G^-$ peaks are sharp, and they originate from LO and TO phonons at Γ point, respectively. Raman shift of $G^+$ peak ($\omega_{G^+}$) do not depend on the tube diameter ($d_{tube}$). On the other hand, that of $G^-$

![Raman scattering spectrum from SWCNTs](image_url)

**Fig. 1.** Raman scattering spectrum from SWCNTs, which were synthesized by using alcohol catalytic CVD (ACCVD) method.\textsuperscript{13} The excitation laser wavelength was 488.0 nm ($E_{ex} = 2.54$ eV).
peak ($\omega_{G^-}$) clearly depend on the tube diameter, because of the curvature effect.\textsuperscript{21} Therefore, the difference of their Raman shift ($\omega_{G^+} - \omega_{G^-}$) is roughly expressed by the tube diameter ($\omega_{G^+} - \omega_{G^-} = C_S/d_{\text{tube}}$, $C_S = 47.7 \text{ cm}^{-1}\text{nm}^2$).\textsuperscript{22} In detail, $\omega_{G^-}$ depends on both the diameter and chiral angle,\textsuperscript{23} as shown in Fig. 2(A).

\begin{figure}[h]
\centering
\includegraphics[width=\textwidth]{fig2.png}
\caption{(A) $G^+$, $G^-$ and RBM peaks of semi-conducting SWCNTs with different chirality, taken from Ref.\textsuperscript{(20)} with permission of Copyright \textcopyright 2016, American Chemical Society. (B) $G^+$ and $G^-$ peaks of metallic SWCNTs under the different gate voltage ($V_g$), taken from Ref.\textsuperscript{(24)} with permission of Benjamin Hatting, et al., \textit{Phys. Rev. B}, \textbf{87}, 165442, 30 April 2013, Copyright by the American Physical Society.}
\end{figure}

For metallic SWCNTs, sharp $G^+$ and broad $G^-$ peaks are observed and they correspond to TO and LO phonons at $\Gamma$ point, respectively. Note that earlier reference imply $G^+$ and $G^-$ peaks correspond to LO and TO phonons even for metallic SWCNTs, respectively. The LO phonon of metallic SWCNTs is softened due to Kohn anomaly,\textsuperscript{25} and the softened and broad (asymmetric) $G^-$ peak of metallic SWCNTs is also called Breit-Wigner-Fano (BWF) peak.\textsuperscript{26} Because of the Kohn anomaly effect, the G-band of metallic SWCNTs is drastically modulated by changing the Fermi energy,\textsuperscript{25,27,28} as shown in Fig. 2(B).

The density of states of SWCNTs exhibits almost discrete energy levels due to van Hove singularity and their optical transition energy ($E_{ii}$) corresponds to the energy gap between two energy states. Raman scattering spectra from SWCNTs are strongly enhanced by resonance Raman effect. If $E_{ii}$ is equal to the energy of incident light ($E_{\text{ex}}$, incident resonance) or that of the scattered light ($E_{\text{ex}} \pm E_{\text{phonon}}$, scattered resonance), Raman scattering intensity becomes large. Here, $E_{\text{ex}} + E_{\text{phonon}}$ and $E_{\text{ex}} - E_{\text{phonon}}$ correspond anti-Stokes and Stokes scatterings,
respectively. Resonance Raman effect\(^{29}\) is expressed by

\[
I (E_{\text{ex}}) \propto \frac{1}{(E_{\text{ex}} - E_{\text{ii}} + i\Gamma)(E_{\text{ex}} \pm E_{\text{phonon}} - E_{\text{ii}} + i\Gamma)}^2 , \tag{1}
\]

where \(\Gamma\) is a resonance window. \(\Gamma\) is a damping constant and is related to the finite lifetime of the intermediate state. In Raman excitation profiles of the G-band, two resonance peaks, which correspond to the incident and scattered resonances, clearly appear with \(\Gamma = 26 - 43\) meV\(^{30}\) for chirality-separated SWCNTs.

Fig. 3. G-band resonance energy profile for (6, 5) and (7, 5) SWCNTs. The black circles are experimental data and the full red line is the present calculation with all matrix elements, while the dashed blue line is the same calculation using constant matrix elements. The electronic gap between the valence and conduction bands was corrected in a few electronvolts to fit with the experimental transitions.\(^{31}\) Figure 3 is taken from Ref. (31) with permission of L. G. Moura, et al., Phys. Rev. B, 89, 035402, 6 January 2014, Copyright by the American Physical Society.

Polarized Raman scattering spectroscopy is performed by using polarized incident and scattered lights, and it provides the information of the phonon symmetry, based on the group theory. The polarization effects of the G-band peaks have been reported.\(^{15}\) In the case of SWCNTs, however, the resonance Raman effect and depolarization effects\(^{32}\) due to the anisotropic geometry of SWCNTs are more prominent than the intrinsic polarization property of Raman scattering.\(^{33}\) As a result, the intensity of the G-band is simply strong when the tube axis is parallel to the polarization of the incident and scattering light. The strong anisotropy is useful for analysis of the tube orientation of SWCNTs.\(^{34}\)

Phonon vibration frequency and Raman shift are affected by isotope abundance. Although the natural abundance of \(^{13}\)C carbon is constant (1.1%), it is possible to synthesize SWCNTs with arbitrary isotope abundance of carbon by using the
carbon source of $^{13}\text{C}\text{.}^{35}$ Raman shift of $^{12}\text{C}$ and $^{13}\text{C}$-SWCNTs is expressed by

$$\omega_{^{13}\text{C}(1-x)^{13}\text{C}x} = \omega_{^{12}\text{C}} \sqrt{\frac{m_{^{12}\text{C}}}{m_{^{12}\text{C}}(1-x) + m_{^{13}\text{C}}x}}$$

where, $\omega_{^{12}\text{C}}$ is the phonon frequency of pure $^{12}\text{C}$-SWCNT, and $\omega_{^{12}\text{C}(1-x)^{13}\text{C}x}$ is the phonon frequency of mixture of $^{12}\text{C}$ and $^{13}\text{C}$-SWCNT, $x$ is $^{13}\text{C}$ atom concentration, $m_{^{12}\text{C}}$ and $m_{^{13}\text{C}}$ are the mass of $^{12}\text{C}$ and $^{13}\text{C}$ carbon atoms, respectively. Equation (2) is available for G-band, D-band and 2D-band, $^{36}$ and the isotope abundance can be investigated by Raman scattering spectroscopy, as shown in Fig. 4.

![Raman spectra](image)

**Fig. 4.** Raman spectra of SWCNTS containing different amount of $^{13}\text{C}$; RBM peaks, D-band, G-band and 2D-band spectral regions, taken from Ref. $^{36}$ with permission of Elsevier.

### 1.2. D-band

The D-band is a defect-induced peak in graphitic structure and the D-band is explained by double resonance effect.$^{37,38}$ Therefore, the intensity ratio between the G-band and D-band is often used for the evaluation of crystallinity of graphitic structure for not only SWCNTs but also multi-walled carbon nanotube and other graphitic carbon materials. Tuinstra-Koening relation$^{14}$

$$\frac{I_D}{I_G} = C(\lambda)/L_D,$$  (3)

where, $I_G$ and $I_D$ are the intensity of the G-band and D-band, respectively, $C(\lambda)$ is the proportionality constant, which depends on the excitation laser wavelength, and $L_D$ is the crystallite size, is used for characterization of the crystallinity of graphitic structure. In the case of graphene, $L_D$ is estimated to be a few nm.$^{39}$

While D-band is the defect-induced peak, it corresponds to a phonon around $K$ point. Double resonance effect$^{37,38}$ involving scattering of phonon around $K$ point
and inelastic scattering with defect structure, causes D-band peak. Because of the double resonance effect, Raman shift of the D-band ($\omega_D$) shows the excitation light energy dependence ($d\omega_D/dE_{ex} \sim 53 \text{ cm}^{-1}\text{eV}^{-1}$).\cite{38}

2D-band is the second-order Raman scattering of D-band phonon and it may be also called G’-band. It also appears due to double resonance effects.\cite{37,38} In the case of 2D-band, inelastic scattering with defects is not required and 2D-band is observed from graphitic materials even without defect structure. Because no defect is involved, some people preferred to call as G’-band rather then 2D-band. The shape of the 2D-band of SWCNTs is different from that of double-walled carbon nanotubes (DWCNTs)\cite{40} and the 2D-band is a signature for distinction between SWCNTs and DWCNTs.

1.3. RBM peaks

![Raman spectra of SDS-wrapped SWCNTs in solution, measured with 76 different laser lines, taken from Ref. (41) with permission of C. Fantini, et al., Phys. Rev. Lett., 93, 147406, 29 September 2004 Copyright by the American Physical Society. Each sharp peaks correspond to different chirality SWCNTs.](image)

RBM peaks appear in the lower wavenumber region. Raman shift of RBM peaks ($\omega_{RBM}$) is inversely proportional to its $d_{\text{tube}}$,\cite{42,43} as follows,

$$\omega_{RBM} = A/d_{\text{tube}}.$$  \hspace{1cm} (4)

Therefore, RBM peaks are often used to analyze the $d_{\text{tube}}$ distribution of SWCNT samples. However, as discussed in Sec. 2.1, $\omega_{RBM}$ is not exactly expressed by Eq. (4), because of the environmental effects on $\omega_{RBM}$. Considering the environmental ef-
fects, the following equation,

\[ \omega_{\text{RBM}} = \frac{A}{d_{\text{tube}}} + B \]  

(5)

is often used. This simple equation is useful for analysis of SWCNT tube diameter, although the values of \( A \) and \( B \) vary depending on the environments, as discussed in Sec. 2.1.

RBM peaks are strongly enhanced by resonance Raman effect and the resonance Raman effect is also expressed by Eq. (1). As shown in Fig. 5, spectra of RBM peaks change with changing the excitation wavelength. Each peaks come from different chirality and the intensity also clearly depend on the chirality. In general, SWCNTs with smaller chiral angle (near zigzag) exhibit stronger intensity of the RBM peaks, as shown in Fig. 6. Additionally, the relationship between the intensity of G+ and RBM peaks is investigated for chirality-separated SWCNT samples and it shows the chirality dependence.
1.4. Kataura plots

As mentioned above, the intensity of RBM peaks is strongly enhanced by resonance Raman scattering effect. The phonon energy of RBM peaks is approximately a few tens of milli electronvolts. When $E_{\text{ex}}$ is in visible or infrared range, $E_{\text{phonon}}$ of RBM peaks is quite small compared with $E_{\text{ex}}$. Therefore, it is usually impossible to distinguish the incident and scattered resonances (Eq. (1)) and only $E_{\text{ii}}$ is simply regarded as the resonance energy in RBM peaks.

The relationship between $\omega_{\text{RBM}}$ and $E_{\text{ii}}$ is called Kataura plot. Figure 7 shows an example of Kataura plot, which is a compilation of experimental data. Because both $\omega_{\text{RBM}}$ and $E_{\text{ii}}$ are roughly proportional to $1/d_{\text{tube}}$, the plots in Fig. 7 appear along lines from the lower left to the top right. Here, the $E_{\text{S}}$ and $E_{\text{M}}$ are the $i$-th optical transition energy of semi-conducting and metallic SWCNTs, respectively. In Fig. 7, five different optical transition energies are shown, such as

![Fig. 7. Empirical Kataura plots of SWCNTs. Blue open circles (○) are measured from as-grown SWCNTs. Blue cross marks (×) are calculated from the empirical equation. Green open circles (○), red open circles (○) and filled circle (●) are measured from dispersed SWCNTs in solution. Green filled circles (●) are measured from suspended SWCNTs. The energy of excitation laser, which is widely used for Raman scattering measurement of SWCNTs, is shown.](image-url)
$E_{11}^S$, $E_{11}^M$, $E_{22}^S$, $E_{33}^S$, and $E_{44}^S$. $E_{ii}$ depends on both $d_{\text{tube}}$ and the chiral angle ($\theta$). Therefore, the plots do not appear just along lines and slightly spread. In Fig. 7, the plots with the same value of $(2n + m)$ are connected with line segments and they show so-called “family pattern”. Some of the plots are shown with chiral index $(n, m)$ or the number of $(2n + m)$. Semi-conducting SWCNTs are often categorized into two groups. Semi-conducting SWCNTs with $(2n + m) \mod 3 = 1$ and $2$ are called ‘type-I’ (‘SI’ or ‘mod2’) and ‘type-II’ (‘SII’ or ‘mod1’) SWCNTs, respectively. Some properties of SWCNTs show the type-dependence. For example, $E_{ii}$ depends on strain and whether $E_{ii}$ increases or decreases is determined by the type.

Based on Kataura plot, it is possible to assign the chirality from measured RBM peaks. When $E_{ii}$ is close to the $E_{\text{ex}}$, the RBM peaks are observed. The resonance window ($\Gamma$) depend on SWCNT samples, such as SDS wrapped SWNTs in solution ($\Gamma = 60$ meV) and bundled SWCNTs ($\Gamma = 120$ meV). According to Kataura plots, for example, RBM peaks in Fig. 1 correspond to semiconducting SWCNTs with $2n + m = 29$ and metallic SWCNTs with $2n + m = 21$.

2. Environmental effects on Kataura plots

The plots of some typical SWCNT samples, such as as-grown SWCNT, which may be bundled, surfactant-wrapped SWCNTs in water solution, and suspended in air, are shown in Fig. 7. Although these plots are slightly different, they show a similar feature. Note that the blue cross marks are calculated from the empirical equation. Additionally, two more kinds of SWCNTs, which are vertically-aligned SWCNTs and suspended SWCNTs in vacuum, are considered and their plots are added in Kataura plot in Fig. 8. These two kinds of SWCNTs are clearly different from former SWCNT samples. $\omega_{\text{RBM}}$ and $E_{ii}$ considerably change depending on the surrounding condition around SWCNTs, which is called “environmental effects”. In the following, the environmental effects on $\omega_{\text{RBM}}$ and $E_{ii}$ are discussed.

2.1. Raman shift

d_{\text{tube}} is geometrically defined by the chirality index $(n, m)$ with the lattice constant $(a_{C-C})$ of the honeycomb structure of carbon atoms, as follows

$$d_{\text{tube}} = \sqrt{3} a_{C-C} \frac{\sqrt{n^2 + nm + m^2}}{\pi}.$$  

$a_{C-C}$ of graphene is 0.142 nm and the value of $a_{C-C} = 0.142$ nm is also used for SWCNTs. Note that the value of $a_{C-C} = 0.144$ nm has often been employed for the calculation of SWCNT diameter. Density functional theory calculation reveals that $a_{C-C}$ depends on $d_{\text{tube}}$ in small $d_{\text{tube}}$ range and $a_{C-C}$ increases with decreasing $d_{\text{tube}}$. $a_{C-C}$ of SWCNTs with 0.6 nm in diameter is approximately 0.144 nm. However, typical $d_{\text{tube}}$ of SWCNTs, which are synthesized experimentally, is 0.7 nm at the smallest (for example (6, 5) SWCNT). For simple comparison, the coefficients
of the equations, such as $A$ in Eq. (4), or $A$ and $B$ in Eq. (5), are re-calculated by using the $a_{C-C} = 0.142\text{ nm}$ instead of $a_{C-C} = 0.144\text{ nm}$.

$\omega_{\text{RBM}}$ is simply proportional to $1/d_{\text{tube}}$.\textsuperscript{42,43} With given the speed of sound in SWCNTs, theory predicts that the value of $A$ is $227\text{ cm}^{-1}\text{nm}$.\textsuperscript{42} In fact, in the case of suspended and isolated SWCNTs in vacuum, the value of $A$ is measured to be $227\text{ cm}^{-1}\text{nm}$\textsuperscript{54} or $228\text{ cm}^{-1}\text{nm}$.\textsuperscript{58} Because suspended SWCNTs in vacuum are perfectly free, they exhibit their intrinsic properties. In isolated and suspended SWCNTs, experimental and theoretical results show good agreement of the diameter dependence of $\omega_{\text{RBM}}$. The same value of $A (227\text{ cm}^{-1}\text{nm})$ is obtained from vertically-aligned SWCNTs.\textsuperscript{59} Hence, vertically-aligned SWCNTs are directly grown on substrates. They vertically stand up on the substrate with entangling each other, and form the small-bundle structure.\textsuperscript{60} The value of $A = 227\text{ cm}^{-1}\text{nm}$ suggests that partially-suspended and isolated SWCNTs exist in vertically-aligned SWCNT samples and they are not covered with any substances.

Generally, as-grown SWCNTs are bundled or interacting with other materials. Therefore, in order to express the relationship between $\omega_{\text{RBM}}$ and $d_{\text{tube}}$, various values of $A$ had been reported. $A = 244.6\text{ cm}^{-1}\text{nm}$ ($A = 248\text{ cm}^{-1}\text{nm}$ with $a_{C-C} = 0.144\text{ nm}$ in the original literature)\textsuperscript{61} was obtained from SWCNTs grown on silicon substrates and $A = 223.75\text{ cm}^{-1}\text{nm}$ was from bundled SWCNT samples.\textsuperscript{62}

As the other type of approximation to express the environmental effects on $\omega_{\text{RBM}}$, Eq. (5) is frequently used. The value of $B$ express the “environmental effect” on $\omega_{\text{RBM}}$, and many combination of the values $(A, B)$ is proposed

![Fig. 8. Relationship between $\omega_{\text{RBM}}$ and the $E_{\text{ii}}$ (Kataura plot) obtained from suspended SWCNTs. The PL and Raman scattering measurements were performed in vacuum (open diamond, ♦) and water vapor (open circle, ◊). The plots of as-grown SWCNTs (x)\textsuperscript{45} and surfactant wrapped SWCNTs in solution (+)\textsuperscript{46} are shown as reference. The open (□)\textsuperscript{45} and filled square (■)\textsuperscript{53} marks present the Raman resonant energy and $\omega_{\text{RBM}}$, which are calculated from the empirical equations for as-grown and vertically aligned SWCNT samples, respectively. Figure 8 is taken from Ref. (54) with permission of S. Chiashi, et al., Phys. Rev. B, 91, 155415, 15 April 2015, Copyright by the American Physical Society.](image-url)
Fig. 9. Raman scattering spectra (G-band and RBM peak) from (10, 5) SWCNT, measured in vacuum (4.0 Pa) and water vapor (630 Pa). The wavelength of the excitation laser is 785 nm. Figure 9 is taken from Ref. (63) with permission of Y. Homma, et al., Phys. Rev. Lett., 110, 157402, 9 April 2013, Copyright by the American Physical Society.

for various SWCNT samples. For example, \( (A, B) = (220.4, 12.5) \) \([(223.5, 12.5)\] with \( a_{C-C} = 0.144 \text{ nm} \) in the original literature\),64 \( (218, 17) \) for metallic SWCNTs and \( (223, 10) \) for semi-conducting SWCNTs,41 \( (214.4, 18.7), 65 (215, 18)\)66 and \( (217.8, 15.7)\)45 are measured from SDS-wraped SWCNTs. \( (A, B) = (204, 27)\)67 is reported for suspended SWCNTs and the value of \( B \) is non-zero in spite of suspended SWCNTs. The non-zero value of \( B \) suggests that the suspended SWCNTs are adsorbed with water layer and the adsorption effects modified \( \omega_{\text{RBM}}\).54 as discussed later. Equation (5) is also available for the case of suspended SWCNTs in vacuum with \( (A, B) = (227, 0) \) or \( (228, 0) \), and it is practically useful for investigation of RBM peaks and estimation of the tube diameter distribution of SWCNTs, although the available surrounding conditions and diameter range should be considered. Note that \( A \) and \( B \) are simply fitting parameters and they do not have physical meanings.

In order to investigate the environmental effect on \( \omega_{\text{RBM}} \), some models are proposed. One is a model, where SWCNT is surrounded by an environmental shell and it is under inward pressure.59 In this model,

\[
\omega_{\text{RBM}} = (A/d_{\text{tube}}) \sqrt{1 + C \times d_{\text{tube}}^2}
\]

(7)

where

\[
C = \frac{6 (1 - \nu^2) K}{Eh \frac{8 \sigma^2}
\]

(8)

is obtained, where \( \nu \) is the Poissons ratio, \( E \) is the Youngs modulus, \( h \) is the thickness of the SWCNT wall, \( K \) is the van der Waals interaction strength, and
$s_0$ is the equilibrium separation between the SWCNT wall and the environment shell. In Eq. (7), the values of $(A, C) = (227, 0.05786)^5$ are available for various SWCNT sample. Of course, Eq. (7) with $(A, C) = (227, 0)$ is available for suspended SWCNTs in vacuum.$^5$

Other one is a model, where SWCNT is wrapped with surrounding media. Assuming that the surrounding media physically adsorb on the outer surface of SWCNTs, the interaction between the SWCNT and the media is regarded to be the van der Waals interaction and the mechanical coupling of radial breathing vibration between SWCNT and the surrounding media causes the environmental effect on $\omega_{\text{RBM}}$. $^5$ $\omega_{\text{RBM}}^{\text{in}} = A/d_{\text{tube}}$ is the intrinsic RBM frequency of SWCNT, $\omega_{\text{ad}}$ is the vibration frequency of radial breathing mode of the surrounding media and $\omega_{\text{RBM}}^{\text{ex}}$ is the extrinsic frequency due to the environmental effects. Based on simple dynamic considerations, the dynamical matrix is

$$
\begin{bmatrix}
(\omega_{\text{ad}})^2 + K_{11} & K_{12} \\
K_{21} & (\omega_{\text{RBM}}^{\text{in}})^2 + K_{22}
\end{bmatrix}
$$

and the matrix gives $\omega_{\text{RBM}}^{\text{ex}}$ as the eigenvalue. $K_{ij}$ is the interaction between SWCNT and the surrounding media and they are calculated by integration of the interaction between the carbon atoms and atoms of the surrounding media. In this model, the environmental effects of SWCNTs (bundle structure) and water adsorption layer as the surrounding media can be calculated with the value of $A = 227 \text{ cm}^{-1} \text{nm}$, and the calculated results show good agreement with the experiments for wide $d_{\text{tube}}$ range.$^5$ RBM peak from suspended (10, 5) SWCNT measured in vacuum and water vapor are shown in Fig. 9. Sharp single RBM peak clearly appears and the peak is up-shifted in water vapor. The up-shift comes from the adsorption of water molecules on the outer surface of SWCNT. Since the interaction between water and SWCNT is not so strong, strain or inward pressure do not occur in suspended SWCNT.

SWCNTs lying on substrates are one of the most typical SWCNT samples, and their $\omega_{\text{RBM}}$ are affected by contact with substrates. However, the substrate effect on $\omega_{\text{RBM}}$ is complicate, because the substrate contact is not axial symmetry, the radical deformation may affect$^6$ and the interaction between SWCNTs and substrates is very diverse. By using suspended SWCNTs over the trench structure, the substrate effect is investigated and $\omega_{\text{RBM}}$ of supported parts, which is in contact with the substrate, is a few cm$^{-1}$ higher than that of suspended parts.$^6$ Axial strain also affects $\omega_{\text{RBM}}$ and 10% tensile strain causes up-shift by a few cm$^{-1}$.$^7$

### 2.2. Resonance energy

In order to determine the resonance Raman energy, Raman scattering spectra are measured by continuously changing the wavelength of excitation light.$^4$ Usually, laser source is used as the excitation light and the different optical systems for each wavelength are needed. Therefore, it is not so easy to measure the resonance
Fig. 10. Emission and excitation wavelengths of surfactant-wrapped SWCNTs (×), suspended SWNTs in air (○) and suspended SWCNTs in vacuum (●). While no substance adsorb on the suspended SWCNTs in vacuum, water molecules adsorb on the outer surface of suspended SWCNTs in air. Figure 10 is taken from Ref. (71) with permission of Copyright © 2008, American Chemical Society.

Raman energy. On the other hand, photoluminescence (PL) spectroscopy is useful tool to measure $E_{ii}$ although PL emission is measured from only semi-conducting SWCNTs. Only by changing the excitation wavelength, PL spectroscopy gives us the information of $E_{ii}$. Additionally, it is reported that Raman excitation profiles of RBM peaks is almost the same as PL emission spectra. Here, assuming that the resonance Raman energy of RBM peaks is simply equal to $E_{ii}$ which are obtained by PL spectroscopy, the environmental effects of the resonance Raman energy is discussed.

$E_{ii}$ is not simply the energy difference between a pair of van Hove singularity peaks in the electronic density of states of SWCNTs. The interaction between excited electron and hole, and between excited electron and the other electrons should be considered and these interactions determine the binding energy of exciton. The binding energy of exciton of SWCNTs is relatively large and the binding energy contributes to $E_{ii}$. The binding energy depends on the dielectric constant, $\epsilon$ because the Coulomb interaction is a function of $\epsilon$. The dielectric constant is affected by the surrounding condition of SWCNTs and it is the one of the origin of the environmental effects of $E_{ii}$. Usually, in the case of SWCNTs, $E_{ii}$ decreases with increasing the dielectric constant.

As mentioned in Sec. 2.1, suspended SWCNTs in vacuum are perfectly free from any substances and they show the intrinsic property of SWCNTs. Their $E_{ii}$ are measured by PL spectroscopy and the value of $E_{ii}$ is larger than those in the other conditions, as shown in Fig. 10. $E_{11}$ and $E_{22}$ of suspended SWCNTs in vacuum are clearly larger than those of suspended SWCNTs in air, which are adsorbed with water layer, and surfactant-wrapped SWCNTs. The same value of $E_{ii}$ is obtained from vertically-aligned SWCNTs. It also suggests the existence of partially suspended and isolated SWCNTs in vertically-aligned SWCNT samples. The environmental effect on $E_{ii}$ is investigated by the immersion of suspended SWCNTs into various liquids. SWCNTs exhibit different $E_{ii}$ depending on the dielectric constant of liquids.
Additionally, the interaction among SWCNTs in bundle structure decreases $E_{ii}$ and increase the resonance Raman window ($\Gamma$). SDS-wrapped SWCNTs is 65 meV, while that of bundled SWCNT is 112 meV. The similar bundling effects on $E_{ii}$ is measured by PL spectroscopy.

Strain changes $E_{ii}$ and the shift of $E_{ii}$ shows type-dependence. Small band gap appears in metallic SWCNTs due to strain. Whether $E_{ii}$ of semi-conducting SWCNTs increases or decreases depends on the value of $p = (n - m) \mod 3$

$$\Delta E = \text{sgn} (2p + 1) 3t_0 [(1 + \nu) \sigma \cos 3\theta + \gamma \sin 3\theta]$$ (10)

where $p = 1$ or $p = -1$ is for type-I or type-II, respectively, $t_0$ is the tight-binding overlap integral, $\nu$ is the Poisson’s ratio, $\sigma$ and $\gamma$ are uniaxial and torsional strains, respectively.

2.3. Temperature dependence

Raman scattering spectra depend on temperature. It is well-known that the intensity ratio between Stokes and anti-Stokes scattering is a function of temperature, as follows

$$\frac{I_{AS}}{I_S} = \exp \left( - \frac{E_{\text{phonon}}}{k_B T} \right)$$ (11)

where $I_S$ and $I_{AS}$ are the intensity of Stokes and anti-Stokes scattering, $k_B$ is the Boltzmann constant, and $T$ is temperature. It is generally possible to obtain the phonon temperature from the intensity ratio. However, in the case of the G-band of SWCNTs, Eq. (11) is not valid. The G-band intensity is strongly enhanced by resonance Raman effect and the phonon energy of the G-band (approximately 0.2 eV) is relatively large. Therefore, the scattered resonance energy is different between Stokes and anti-Stokes ($E_{ex} \pm E_{\text{phonon}}$) and Raman excitation profiles are also different.

Although Eq. (11) is not available for the G-band, it is possible to measure the SWCNT temperature from Raman shift of the G-band. Generally, with increasing temperature, Raman shift decreases and the peak width increases because of nonharmonic component of lattice vibration. Raman shift of the G-band decreases with increasing temperature and the temperature dependence of the G$^+$ peak is simply expressed by

$$\omega_{G^+}(T) = \omega_0 - \frac{a}{\exp \left( \frac{b \omega_0}{k_B T} \right) - 1}$$ (12)

where $h (= 2\pi \hbar)$ is the Planck constant and $a$, $b$ and $\omega_0$ are fitting parameters. $a = 38.4 \text{ cm}^{-1}$, $b = 0.438$ and $\omega_0 = 1594 \text{ cm}^{-1}$ are valid in the wide temperature range (form 0 to 1000 K). In Fig. 11, the temperature dependence of $\omega_{G^+}$ measured from different SWCNT samples and the curve calculated by Eq. (12) are shown.

In Kataura plot, the temperature dependence is important, because both $\omega_{RBM}$ and $E_{ii}$ depend on temperature. RBM peaks exhibit downshift of Raman shift and broadening of peak and $E_{ii}$ also decrease width with increasing temperature.
Fig. 11. Temperature dependence of Raman shifts of G+ peaks for various SWNT samples measured with a 488.0 nm excitation laser and for HiPco sample measured with three excitation lasers (488.0, 514.5, and 632.8 nm). The dashed line is a fitting line calculated using Eq. (12). The graph is taken from Ref. 80.

The temperature dependence of $E_{ii}$ of semi-conducting SWCNTs is investigated by PL spectroscopy, 82 and the energy shift of $E_{ii}$ ($\Delta E_{ii}$) is expressed by Varshni equation, as follows

$$\Delta E_{ii}(T) = -\alpha T^2 \frac{1}{T + \beta}$$  \hspace{1cm} (13)

where, $\alpha$ and $\beta$ are the constants. While $\alpha = 0.075 \text{ meV/K}$ and $\beta = 600 \text{ K}$ are obtained in the case of $E_{11}$ of suspended (12, 2) SWCNT in lower temperature range, 82 $\alpha = 0.177 \text{ meV/K}$ and $\beta = 1800 \text{ K}$ are measured from suspended SWCNTs with various chiralities in the higher temperature range. 83 The temperature dependence of $\omega_{RBM}$ is also reported. The obtained values of $\partial \omega_{RBM} / \partial T$ are diverse, such as $-0.013$ and $-0.015 \text{ cm}^{-1}/\text{K}$, 84 $-0.0045$ and $-0.009 \text{ cm}^{-1}/\text{K}$, 78 $\sim 0.006 \text{ cm}^{-1}$, 79 and $-0.001 \sim -0.015 \text{ cm}^{-1}/\text{K}$. 80

Temperature increase often occurs during Raman scattering measurement. The optical absorption cross-section of SWCNTs is a few $10 \times 10^{18} \text{ cm}^2/\text{atom}$ at the $E_{ii}$ (on-resonance). 85 The temperature of SWCNTs under light irradiation is determined by the power density of excitation light, the light absorption cross-section, the thermal conductivity and the thermal conductance between SWCNTs and the surrounding system. Especially, the temperature of SWCNTs is easily increased in the cases of SWCNTs in vacuum, on substrates with low thermal conductivity and
suspended SWCNTs. During the measurement in atmospheric ambient, it is possible that SWCNTs under light irradiation are damaged or burned by oxidization. Even without damage, the temperature dependence of $E_i$ and $\omega_{\text{RBM}}$ could appear in RBM spectra.

3. Acknowledgments

This work is supported by JSPS KAKENHI Grant numbers JP15H05760, JP16H02079 and JP18H05329, Japan and by JST CREST Grant Number JP-MJCR17I3, Japan. We would like to thank Ms. Pengyingkai Wang at UTokyo for her technical help in manuscript preparation.

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